# Waveguide-integrated modulators and photodetectors based on high mobility hBNgraphene-hBN heterostructures

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Photodetectors and optical modulators are key components in today's communication systems<sup>[1]</sup> for which graphene promises a broadband response, high switching rates and an extremely small footprint. In this work, we report the experimental results and numerical simulations on waveguideintegrated photodetectors and electroabsorption (EA) modulators, both based on high mobility hexagonal boron nitride (hBN) encapsulated graphene.

In order to reach a low voltage drive, the double layer graphene modulators have been fabricated in combination with a high-K dielectric material, e.g. hafnia (HfO<sub>2</sub>) <sup>[2]</sup>. The resulting hBN-HfO<sub>2</sub>-hBN insulating layer (see Fig. 1a) ensures increased breakdown voltages and low operation fields while maintaining the high carrier mobility and low doping levels intrinsic to hBN-encapsulated graphene <sup>[3]</sup>. During this work, we systematically studied the dielectric characteristics of this hBN-HfO<sub>2</sub>-hBN insulating combination.

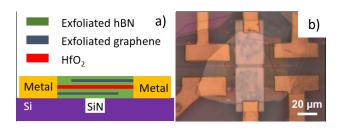
Owing to recent advances in fabrication techniques<sup>[4]</sup>, we achieved large-scale exfoliated hBN-graphene-hBN

photodetectors with active areas up to 100 µm<sup>2</sup>. These large scale devices (see Fig. 1b) allow for the systematic study of the responsivity as a function of the devices' dimension. Specifically, we investigate the effect of the source-to-drain distance and the length of the absorption area (Fig. 1b). The experimental results are compared to simulations.

### References

- [1] G.T. Reed et al., Nature Photon. 4 (2010) 518-526.
- [2] Y. Hattori et al. ACS Appl. Mater. Interfaces, 8 (2016), 41.
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- [4] F. Pizzocchero et al. Nature Comm. 7 (2016) 11894.

### Figures



**Figure 1:** a) Sketch of a double layer graphene EA modulator with a hBN-HfO<sub>2</sub>-hBN dielectric serat. b) hBN-graphene-hBN based photodetector transferred over an optical waveguide. The length of the active area is around 30 µm.